

FGA180N33ATD

330 V PDP Trench IGBT

Features

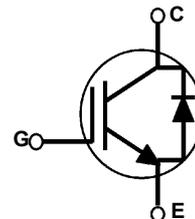
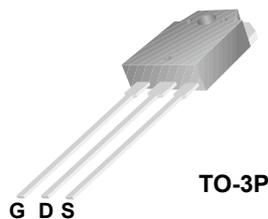
- High Current Capability
- Low Saturation Voltage: $V_{CE(sat)} = 1.68 \text{ V @ } I_C = 180 \text{ A}$
- High Input Impedance
- RoHS Compliant

Applications

- PDP TV

General Description

Using novel trench IGBT Technology, Fairchild®'s new series of trench IGBTs offer the optimum performance for PDP TV applications where low conduction and switching losses are essential.



Absolute Maximum Ratings

Symbol	Description	Ratings	Unit
V_{CES}	Collector to Emitter Voltage	330	V
V_{GES}	Gate to Emitter Voltage	± 30	V
I_C	Collector Current @ $T_C = 25^\circ\text{C}$	180	A
$I_{CM(1)}$	Pulsed Collector Current @ $T_C = 25^\circ\text{C}$	450	A
P_D	Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$	390	W
	Maximum Power Dissipation @ $T_C = 100^\circ\text{C}$	156	W
T_J	Operating Junction Temperature	-55 to +150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds	300	$^\circ\text{C}$

Notes:

1: Repetitive test, pulse width = 100usec, Duty = 0.1

* I_{C_pulse} limited by max T_J

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}(\text{IGBT})$	Thermal Resistance, Junction to Case	-	0.32	$^\circ\text{C/W}$
$R_{\theta JC}(\text{Diode})$	Thermal Resistance, Junction to Case	-	0.82	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	-	40	$^\circ\text{C/W}$

Package Marking and Ordering Information

Device Marking	Device	Package	Packaging Type	Qty per Tube	Max Qty per Box
FGA180N33ATD	FGA180N33ATDTU	TO-3P	Tube	30ea	-

Electrical Characteristics of the IGBT T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
V_{CES}	Collector to Emitter Breakdown Voltage	$V_{GE} = 0V, I_C = 400\mu A$	330	-	-	V
I_{CES}	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0V$	-	-	400	μA
I_{GES}	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0V$	-	-	± 400	nA
On Characteristics						
$V_{GE(th)}$	G-E Threshold Voltage	$I_C = 250\mu A, V_{CE} = V_{GE}$	2.5	4.0	5.5	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C = 40A, V_{GE} = 15V$	-	1.1	1.4	V
		$I_C = 180A, V_{GE} = 15V,$	-	1.68	-	V
		$I_C = 180A, V_{GE} = 15V$ $T_C = 125^\circ C$	-	1.89	-	V
Dynamic Characteristics						
C_{ies}	Input Capacitance	$V_{CE} = 30V, V_{GE} = 0V,$ $f = 1MHz$	-	3880	-	pF
C_{oes}	Output Capacitance		-	305	-	pF
C_{res}	Reverse Transfer Capacitance		-	180	-	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 200V, I_C = 40A,$ $R_G = 5\Omega, V_{GE} = 15V,$ Resistive Load, $T_C = 25^\circ C$	-	27	-	ns
t_r	Rise Time		-	80	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	108	-	ns
t_f	Fall Time		-	180	240	ns
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 200V, I_C = 40A,$ $R_G = 5\Omega, V_{GE} = 15V,$ Resistive Load, $T_C = 125^\circ C$	-	26	-	ns
t_r	Rise Time		-	75	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	112	-	ns
t_f	Fall Time		-	250	300	ns
Q_g	Total Gate Charge	$V_{CE} = 200V, I_C = 40A,$ $V_{GE} = 15V$	-	169	-	nC
Q_{ge}	Gate to Emitter Charge		-	22	-	nC
Q_{gc}	Gate to Collector Charge		-	69	-	nC

Electrical Characteristics of the Diode $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max	Unit	
V_{FM}	Diode Forward Voltage	$I_F = 20\text{A}$	$T_C = 25^\circ\text{C}$	-	1.2	1.6	V
			$T_C = 125^\circ\text{C}$	-	1.04	-	
t_{rr}	Diode Reverse Recovery Time	$I_{ES} = 20\text{A},$ $di/dt = 200\text{A}/\mu\text{s}$	$T_C = 25^\circ\text{C}$	-	27	-	ns
			$T_C = 125^\circ\text{C}$	-	39	-	
I_{rr}	Diode Peak Reverse Recovery Current	$I_{ES} = 20\text{A},$ $di/dt = 200\text{A}/\mu\text{s}$	$T_C = 25^\circ\text{C}$	-	3.5	-	A
			$T_C = 125^\circ\text{C}$	-	6.0	-	
Q_{rr}	Diode Reverse Recovery Charge	$I_{ES} = 20\text{A},$ $di/dt = 200\text{A}/\mu\text{s}$	$T_C = 25^\circ\text{C}$	-	48	-	nC
			$T_C = 125^\circ\text{C}$	-	117	-	

Typical Performance Characteristics

Figure 1. Typical Output Characteristics

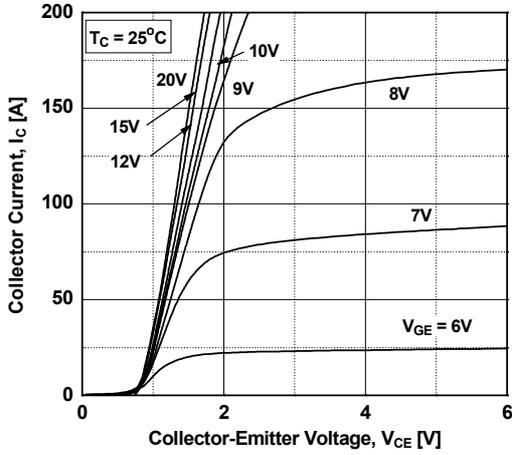


Figure 2. Typical Output Characteristics

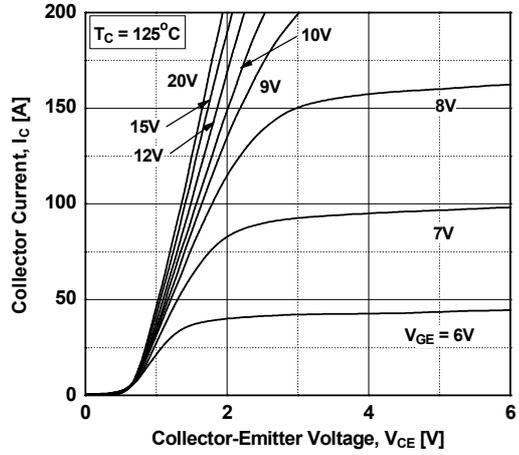


Figure 3. Typical Saturation Voltage Characteristics

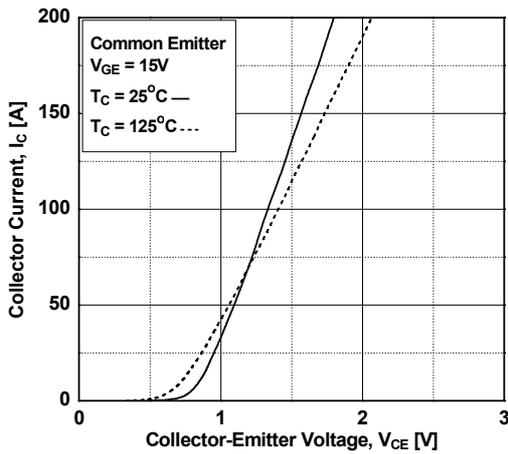


Figure 4. Transfer Characteristics

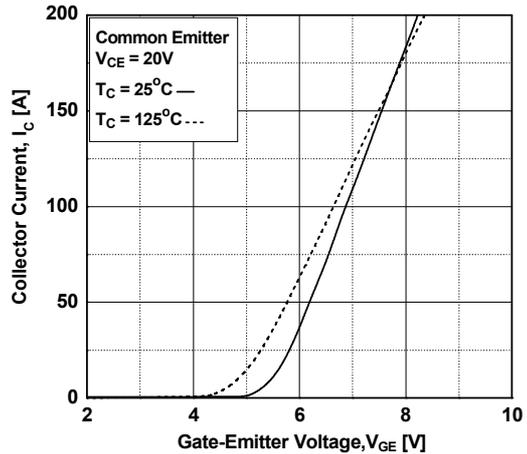


Figure 5. Saturation Voltage vs. Case Temperature at Variant Current Level

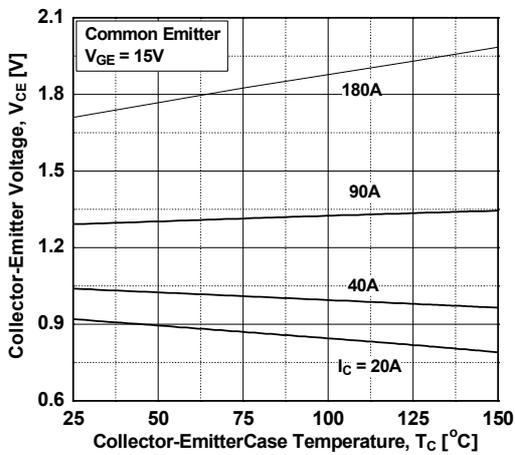
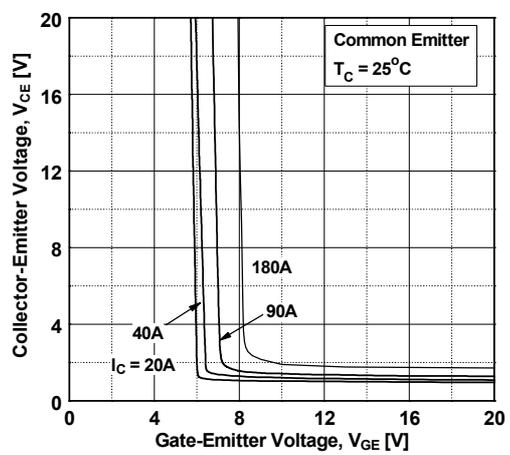


Figure 6. Saturation Voltage vs. Vge



Typical Performance Characteristics

Figure 7. Saturation Voltage vs. V_{GE}

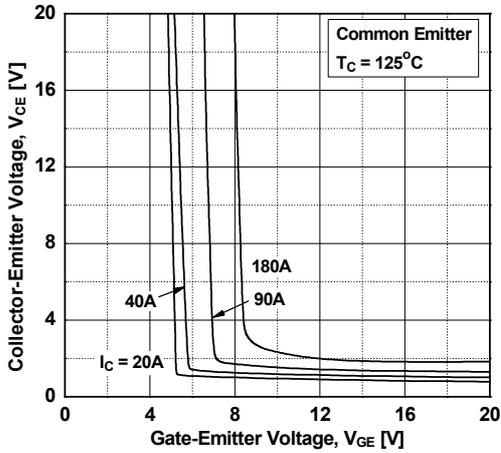


Figure 8. Capacitance Characteristics

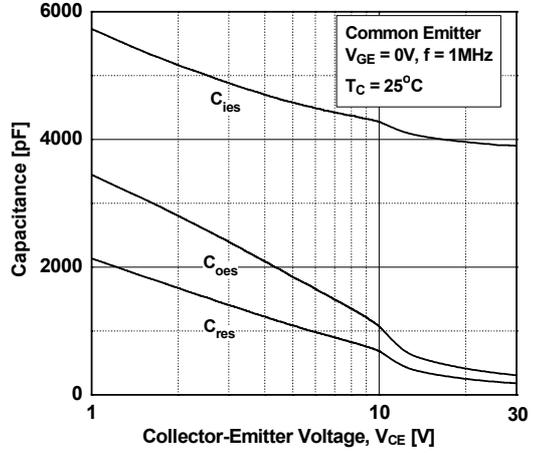


Figure 9. Gate charge Characteristics

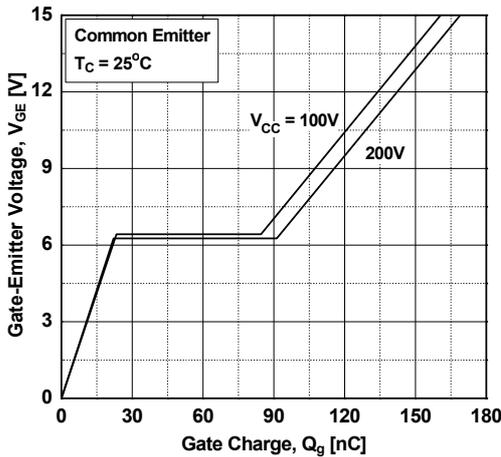


Figure 10. SOA Characteristics

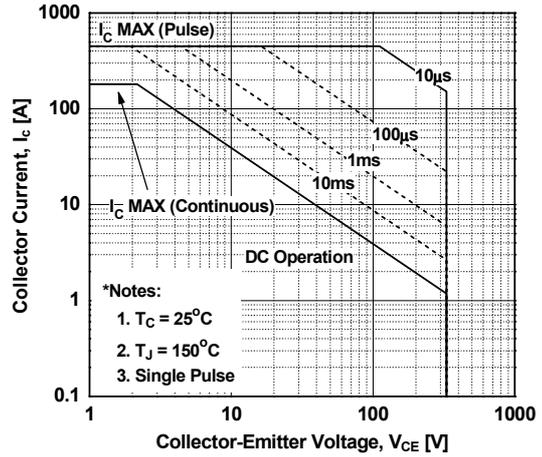


Figure 11. Turn-on Characteristics vs. Gate Resistance

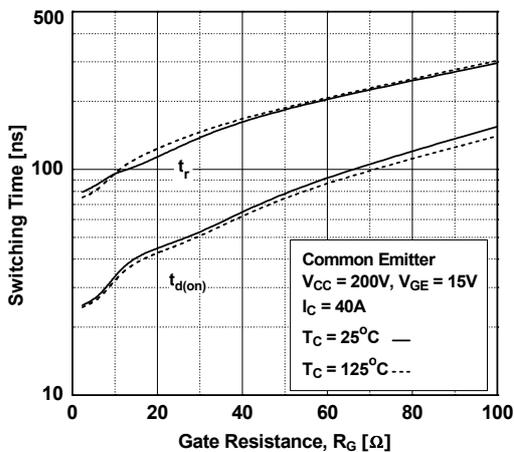
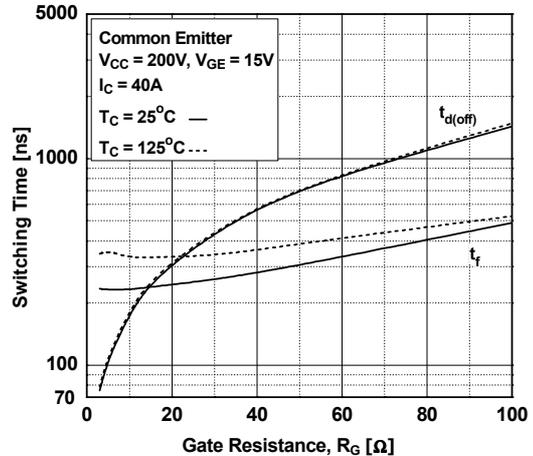


Figure 12. Turn-off Characteristics vs. Gate Resistance



Typical Performance Characteristics

Figure 13. Turn-on Characteristics vs. Collector Current

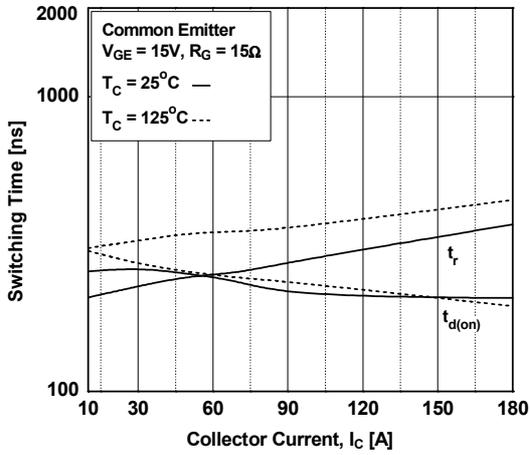


Figure 14. Turn-off Characteristics vs. Collector Current

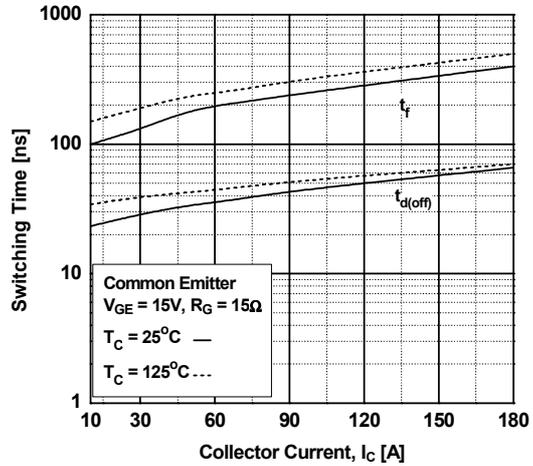


Figure 15. Turn off Switching SOA Characteristics

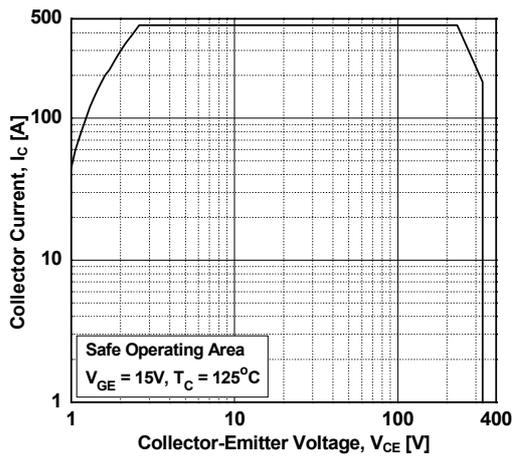
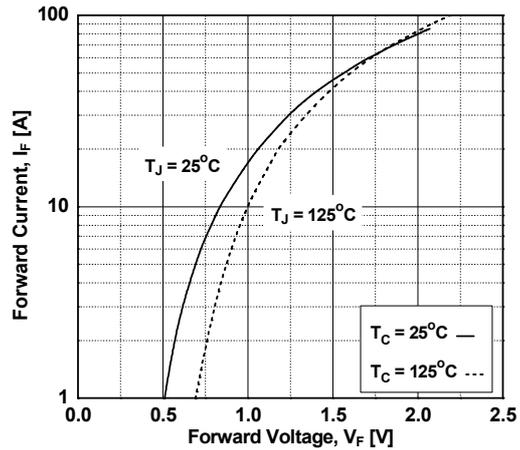


Figure 16. Forward Characteristics



Typical Performance Characteristics

Figure 19. Reverse Recovery Current

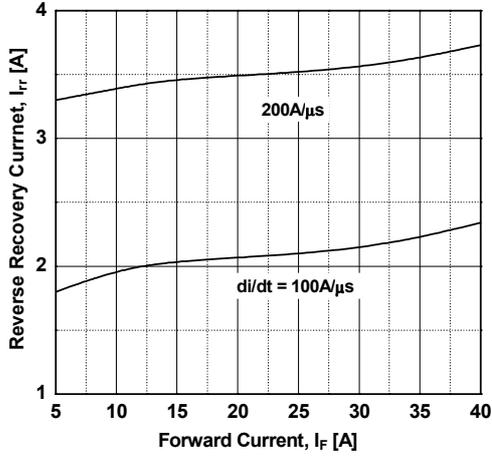


Figure 20. Stored Charge

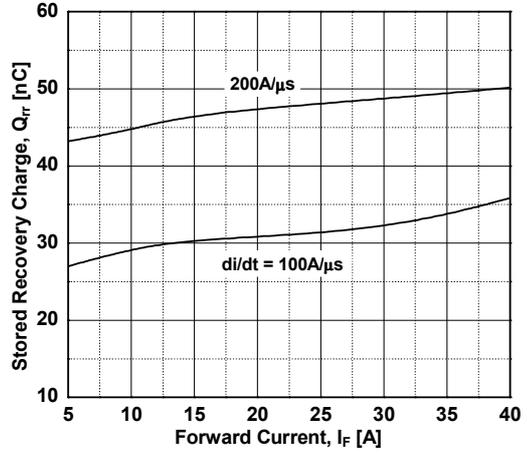


Figure 21. Reverse Recovery Time

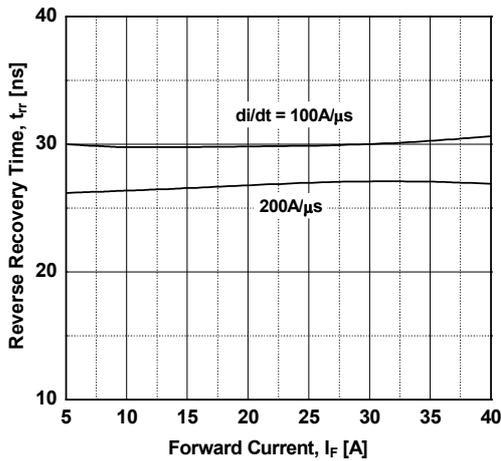
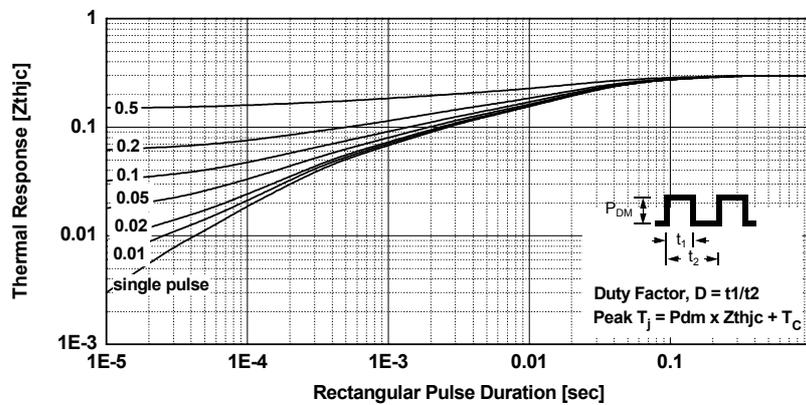
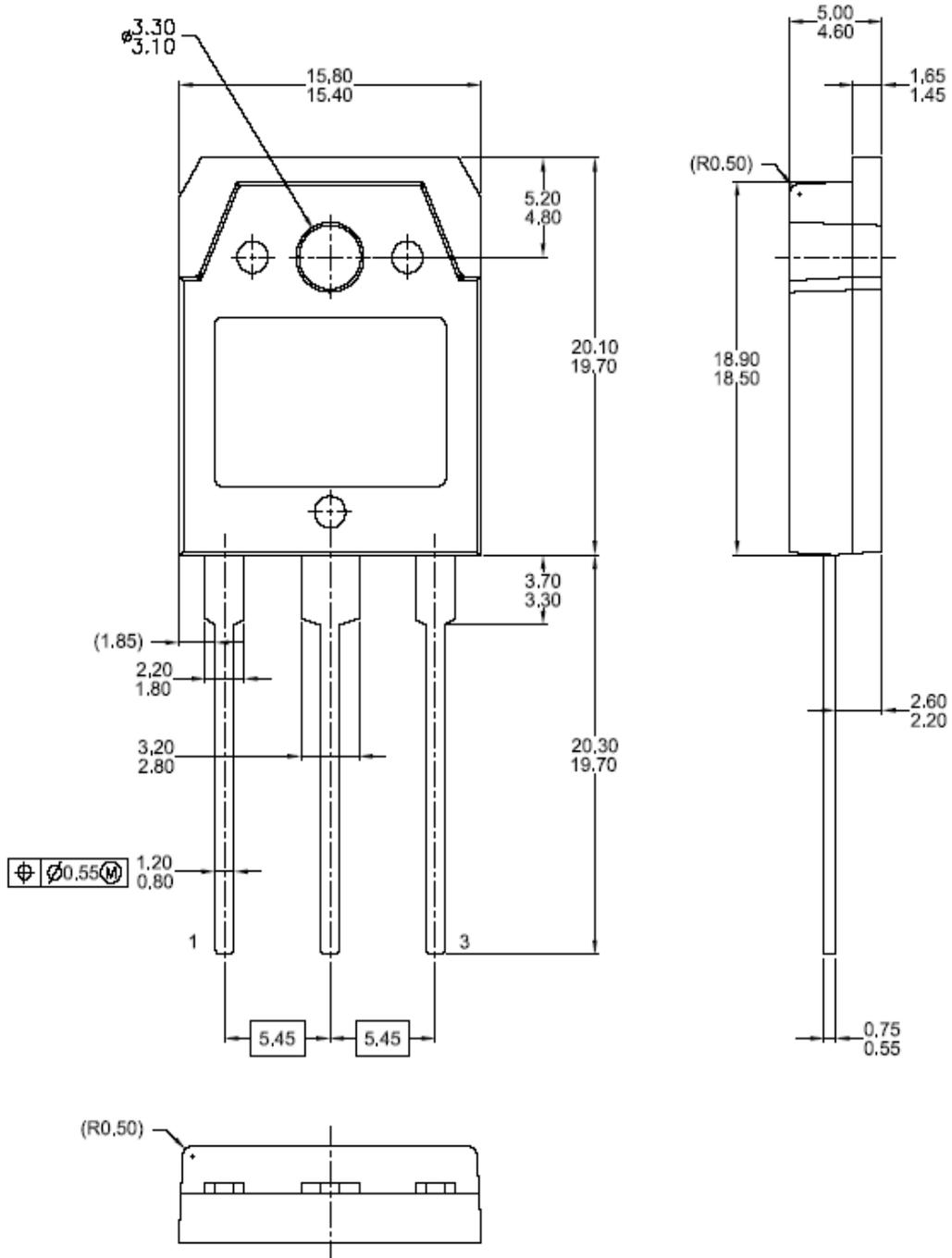


Figure 22. Transient Thermal Impedance of IGBT



Mechanical Dimensions

TO-3PN

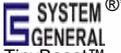


Dimensions in Millimeters



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